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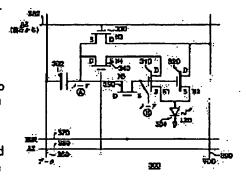
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## (54) ACTIVE MATRIX LIGHT EMITTING DIODE PICTURE ELEMENT STRUCTURE AND METHOD

## (57) Abstract:

PROBLEM TO BE SOLVED: To reduce uneveness of a current in a light emitting diode(LED) so as to improve uniformity of luminance by composing picture element structure of NMOS transistors, a capacitor and the LED.

SOLUTION: Picture element structure 300 is composed of five NMOS transistors 310–350, a capacitor 302 and an LED 304. A selection line 370 is connected to a gate of the transistor 350, and a data line 360 is connected to one terminal of the capacitor 302. An auto-zero line 380 is connected to a gate of the transistor 340, and a VDD line 390 is connected to the drains of the transistors 320, 220. One terminal of the capacitor 302 is connected to the source of the transistor 330 and the drains of the transistors 340, 350, and the sources of the transistors 310, 320 are connected to one terminal of the LED 304. With this constitution, unevenness of a current can be reduced in the LED 304.



## **LEGAL STATUS**

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